

Man Wong

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

206
papers

2,692
citations

29
h-index

44
g-index

240
ext. papers

3,057
ext. citations

2.7
avg, IF

5.07
L-index

#	Paper	IF	Citations
206	Effect of Interface Modification Conditions on Electrical Characteristics and Device Consistency of Organic Thin Film Transistors. <i>IEEE Electron Device Letters</i> , 2022 , 43, 36-39	4.4	
205	Fluorinated Metal-Oxide Thin-Film Transistors for Circuit Implementation on a Flexible Substrate 2022 , 1-1		3
204	Evaluation of Positive-Bias-Stress-Induced Degradation in InSnZnO Thin-Film Transistors by Low Frequency Noise Measurement. <i>IEEE Electron Device Letters</i> , 2022 , 1-1	4.4	2
203	Neuromorphic Implementation of Logic Functions Based on Parallel Dual-Gate Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2022 , 1-1	4.4	3
202	Low-Frequency Noise in Bridged-Grain Polycrystalline Silicon Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2022 , 69, 1984-1988	2.9	1
201	Self-Compensation Effect of Photo-Bias Instabilities in a-InGaZnO Thin-Film Transistors Induced by Unique Ion Migration. <i>IEEE Transactions on Electron Devices</i> , 2022 , 1-7	2.9	1
200	A Comparative Study on Inverters Built With Dual-Gate Thin-Film Transistors Based on Depletion- or Enhancement-Mode Technologies. <i>IEEE Transactions on Electron Devices</i> , 2022 , 1-6	2.9	1
199	Elevated-Metal Metal-Oxide Thin-Film Transistors: A Back-Gate Transistor Architecture with Annealing-Induced Source/Drain Regions 2022 , 273-313		
198	Compact Integration of Hydrogen Resistant aInGaZnO and PolySi Thin Film Transistors. <i>Micromachines</i> , 2022 , 13, 839	3.3	0
197	Reliability of Poly-Si TFTs under Voltage Pulse with Fast Transition Time. <i>IEEE Electron Device Letters</i> , 2021 , 1-1	4.4	2
196	A Unified Degradation Model of Elevated-Metal Metal Oxide (EMMO) TFTs Under Positive Gate Bias With or Without an Illumination. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 1081-1087	2.9	1
195	Enhanced Thermal Stability of Elevated-Metal Metal-Oxide Thin-Film Transistors via Low-Temperature Nitrogen Post-Annealing. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 1649-1653	2.9	6
194	A cost-effective fluorination method for enhancing the performance of metal oxide thin-film transistors. <i>Journal of the Society for Information Display</i> , 2021 , 29, 318-327	2.1	
193	P-19: Student Poster: Enhanced Elevated-Metal Metal-Oxide Thin-Film Transistors for Gate-Driver Circuit Fabricated on a Flexible Substrate. <i>Digest of Technical Papers SID International Symposium</i> , 2021 , 52, 1124-1127	0.5	
192	8-1: Distinguished Paper: A Cost-Effective Fluorination Method for Enhancing the Performance of Metal Oxide Thin-Film Transistors Using a Fluorinated Planarization Layer. <i>Digest of Technical Papers SID International Symposium</i> , 2021 , 52, 77-80	0.5	
191	P-18: Student Poster: Non-Oxidizing Pre-Annealing for Enhanced Fluorination of an Indium-Gallium-Zinc Oxide Thin-Film Transistor. <i>Digest of Technical Papers SID International Symposium</i> , 2021 , 52, 1120-1123	0.5	
190	P-11: Self-Heating Induced Degradation in a Metal-Oxide Thin-Film Transistor on a Flexible Substrate and Its Mitigation. <i>Digest of Technical Papers SID International Symposium</i> , 2021 , 52, 1092-1095	0.5	1

189	P-1.1: Characterization of the Off-State Current of an Elevated-Metal Metal-Oxide Thin-Film Transistor. <i>Digest of Technical Papers SID International Symposium, 2021, 52, 413-416</i>	0.5	4
188	Thermal Budget Reduction in Metal Oxide Thin-Film Transistors via Planarization Process. <i>IEEE Electron Device Letters, 2021, 42, 180-183</i>	4.4	1
187	29.5: Reliability Enhancement of an Indium-Gallium-Zinc Oxide Thin-Film Transistor by Pre-Fluorination Non-Oxidizing Annealing. <i>Digest of Technical Papers SID International Symposium, 2021, 52, 403-406</i>	0.5	
186	2.2: High-Resolution Active-Matrix Organic Light-Emitting Diode Display Realized Using Elevated-Metal Metal-Oxide Transistor Technology. <i>Digest of Technical Papers SID International Symposium, 2021, 52, 51-51</i>	0.5	
185	15.1: Invited Paper: A Low-Temperature Elevated-Metal Metal-Oxide Thin-Film Transistor Technology for Flexible Electronics. <i>Digest of Technical Papers SID International Symposium, 2021, 52, 202-205</i>	0.5	0
184	P-1.2: All-Oxide Thin-Film Transistors for Low-Voltage-Operation Circuits. <i>Digest of Technical Papers SID International Symposium, 2021, 52, 688-691</i>	0.5	
183	Reliable High-Performance Amorphous InGaZnO Schottky Barrier Diodes With Silicon Dioxide Passivation Layer. <i>IEEE Electron Device Letters, 2021, 42, 1338-1341</i>	4.4	1
182	Stacked-Interconnect for Monolithic Integration of Low-Temperature Polysilicon and Amorphous Metal-Oxide Thin-Film Transistors. <i>IEEE Electron Device Letters, 2021, 42, 1331-1333</i>	4.4	1
181	Ultraviolet to Near-Infrared Broadband Phototransistors Based on Hybrid InGaZnO/C8-BTBT Heterojunction Structure. <i>IEEE Electron Device Letters, 2021, 1-1</i>	4.4	1
180	24-2: Distinguished Student Paper: Fluorination for Enhancing the Resistance of Indium-Gallium-Zinc Oxide Thin-Film Transistor against Hydrogen-Induced Degradation. <i>Digest of Technical Papers SID International Symposium, 2020, 51, 347-350</i>	0.5	1
179	Extracting the Critical Breakdown Electrical Field of Amorphous Indium-Gallium-Zinc-Oxide From the Avalanche Breakdown of n-Indium-Gallium-Zinc-Oxide/p+-Nickel-Oxide Heterojunction Diode. <i>IEEE Electron Device Letters, 2020, 41, 1017-1020</i>	4.4	4
178	Fluorinated indium-gallium-zinc oxide thin-film transistor with reduced vulnerability to hydrogen-induced degradation. <i>Journal of the Society for Information Display, 2020, 28, 520-527</i>	2.1	3
177	Suppression of the Short-Channel Effect in Dehydrogenated Elevated-Metal Metal- Oxide (EMMO) Thin-Film Transistors. <i>IEEE Transactions on Electron Devices, 2020, 67, 3001-3004</i>	2.9	8
176	Reversely-Synchronized-Stress-Induced Degradation in Polycrystalline Silicon Thin-Film Transistors and Its Suppression by a Bridged-Grain Structure. <i>IEEE Electron Device Letters, 2020, 41, 1213-1216</i>	4.4	3
175	A Novel Envelope Detector Based on Unipolar Metal-Oxide TFTs. <i>IEEE Transactions on Circuits and Systems II: Express Briefs, 2020, 67, 2367-2371</i>	3.5	6
174	Resilience of Fluorinated Indium-Gallium-Zinc Oxide Thin-Film Transistor Against Hydrogen-Induced Degradation. <i>IEEE Electron Device Letters, 2020, 41, 729-732</i>	4.4	10
173	A High Gain Low-Noise Amplifier Based on ITO-Stabilized ZnO Thin-Film Transistors. <i>IEEE Transactions on Electron Devices, 2020, 67, 5537-5543</i>	2.9	2
172	High-Performance Polycrystalline Silicon Thin-Film Transistors without Source/Drain Doping by Utilizing Anisotropic Conductivity of Bridged-Grain Lines. <i>Advanced Electronic Materials, 2020, 6, 1900961</i>	6.4	4

171	Low Leakage Current Vertical Thin-Film Transistors With InSnO-Stabilized ZnO Channel. <i>IEEE Electron Device Letters</i> , 2020 , 41, 248-251	4.4	6
170	A Timing Model for the Optimal Design of a Prototype Active-Matrix Display. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 3167-3174	2.9	2
169	P-4: Enhanced Scalability and Reliability of High Mobility Elevated-Metal Metal-Oxide Thin-Film Transistors with Bandgap Engineering. <i>Digest of Technical Papers SID International Symposium</i> , 2020 , 51, 1322-1325	0.5	1
168	Dimension Scaling Effects on Conduction and Low Frequency Noise Characteristics of ITO-Stabilized ZnO Thin Film Transistors. <i>IEEE Journal of the Electron Devices Society</i> , 2020 , 8, 435-441	2.3	
167	A Planar Single-Actuator Bi-Stable Switch Based on Latch-Lock Mechanism 2019 ,		1
166	Degradation Induced by Forward Synchronized Stress in Poly-Si TFTs and Its Reduction by a Bridged-Grain Structure. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1467-1470	4.4	6
165	P-11: Carrier Concentration Reduction by Fluorine Doping in P-Type SnO Thin-Film Transistors. <i>Digest of Technical Papers SID International Symposium</i> , 2019 , 50, 1251-1254	0.5	2
164	P-15: Gate-Bias-Stress-Induced Instability in Hybrid-Phase Microstructural ITO-Stabilized ZnO TFTs. <i>Digest of Technical Papers SID International Symposium</i> , 2019 , 50, 1267-1270	0.5	
163	Gate Insulator Engineering in Top-Gated Indium-Tin-Oxide-Stabilized ZnO Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1104-1107	4.4	2
162	1.3: A Timing Model for the Design of an Active-Matrix Display. <i>Digest of Technical Papers SID International Symposium</i> , 2019 , 50, 13-16	0.5	
161	8.2: Invited Paper: Elevated-Metal Metal-Oxide Thin-Film Transistor with Self-Aligned Source/Drain Regions. <i>Digest of Technical Papers SID International Symposium</i> , 2019 , 50, 75-78	0.5	
160	Low-Temperature-Processed Power Schottky Diode Based on Amorphous Indium-Tin-Zinc-Oxide/Indium-Gallium-Zinc-Oxide Bilayer. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 4759-4763	2.9	5
159	Compact Modeling of Thin-Film Transistors for Flexible Hybrid IoT Design. <i>IEEE Design and Test</i> , 2019 , 36, 6-14	1.4	8
158	Self-Aligned Elevated-Metal Metal-Oxide Thin-Film Transistors for Displays and Flexible Electronics 2019 ,		7
157	Low-Power Design for Unipolar ITO-Stabilized ZnO TFT RFID Code Generator Using Differential Logic Decoder. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 4768-4773	2.9	9
156	A Comparative Study on Fluorination and Oxidation of Indium-Gallium-Zinc Oxide Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2018 , 39, 196-199	4.4	22
155	Realization and Characterization of a Bulk-Type All-Silicon High Pressure Sensor. <i>Journal of Microelectromechanical Systems</i> , 2018 , 27, 231-238	2.5	3
154	Fluorination-Enabled Monolithic Integration of Enhancement- and Depletion-Mode Indium-Gallium-Zinc Oxide TFTs. <i>IEEE Electron Device Letters</i> , 2018 , 39, 692-695	4.4	19

153	Passivation of Poly-Si Thin Film Employing Si Self-Implantation and Its Application to TFTs. <i>IEEE Journal of the Electron Devices Society</i> , 2018 , 6, 240-244	2.3	1
152	A Physical Model for MetalOxide Thin-Film Transistor Under Gate-Bias and Illumination Stress. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 142-149	2.9	9
151	Investigation of top gate GaN thin-film transistor fabricated by DC magnetron sputtering. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2018 , 36, 032203	1.3	3
150	Suppressed Degradation of Elevated-Metal MetalOxide Thin-Film Transistors Under Bipolar Gate Pulse Stress. <i>IEEE Electron Device Letters</i> , 2018 , 39, 707-710	4.4	8
149	Three-Mask Elevated-Metal Metal-Oxide Thin-Film Transistor With Self-Aligned Definition of the Active Island. <i>IEEE Electron Device Letters</i> , 2018 , 39, 35-38	4.4	4
148	Threshold Voltage Adjustment in Hybrid-Microstructural ITO-Stabilized ZnO TFTs via Gate Electrode Engineering. <i>IEEE Electron Device Letters</i> , 2018 , 39, 975-978	4.4	9
147	. <i>IEEE Electron Device Letters</i> , 2018 , 39, 1338-1341	4.4	2
146	P-15: The Use of Fluorination to Enhance the Performance and the Reliability of Elevated-Metal Metal-Oxide Thin-Film Transistors. <i>Digest of Technical Papers SID International Symposium</i> , 2018 , 49, 1235-1238 ¹⁰	0.5	10
145	P-130: Reliable Flexible Elevated Metal Metal-Oxide IGZO TFTs. <i>Digest of Technical Papers SID International Symposium</i> , 2018 , 49, 1587-1589	0.5	1
144	P-1.5: Edge Effects of Three-Mask Elevated-Metal Metal-Oxide Thin-Film Transistor and Their Elimination. <i>Digest of Technical Papers SID International Symposium</i> , 2018 , 49, 531-534	0.5	1
143	The Implementation of Fundamental Digital Circuits With ITO-Stabilized ZnO TFTs for Transparent Electronics. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 5395-5399	2.9	6
142	8.1: Invited Paper: Enhanced Elevated-Metal Metal-Oxide Thin-Film Transistor Technology. <i>Digest of Technical Papers SID International Symposium</i> , 2018 , 49, 75-78	0.5	1
141	P-1.4: Elevated-Metal Metal-Oxide Thin-Film Transistor with Fluorinated Indium-Gallium-Zinc Oxide Channel towards Flexible Applications. <i>Digest of Technical Papers SID International Symposium</i> , 2018 , 49, 528-530	0.5	
140	24.3: Short-Channel Indium-Gallium-Zinc Oxide Thin-Film Transistor Enabled by Thermal Dehydrogenation and Oxidizing Defect-Suppression. <i>Digest of Technical Papers SID International Symposium</i> , 2018 , 49, 255-258	0.5	
139	30.1: Transparent Basic Logic Circuits with ITO-Stabilized ZnO Thin Film Transistors. <i>Digest of Technical Papers SID International Symposium</i> , 2018 , 49, 322-325	0.5	
138	OFF-State-Stress-Induced Instability in Switching Polycrystalline Silicon Thin-Film Transistors and Its Improvement by a Bridged-Grain Structure. <i>IEEE Electron Device Letters</i> , 2018 , 39, 1684-1687	4.4	7
137	A Bottom-Gate MetalOxide Thin-Film Transistor With Self-Aligned Source/Drain Regions. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 2820-2826	2.9	11
136	P-21: Three-Mask Elevated-Metal Metal-Oxide Thin-Film Transistor Technology for High-Resolution AMOLED Application. <i>Digest of Technical Papers SID International Symposium</i> , 2018 , 49, 1256-1259	0.5	

135	Characteristics of Elevated-Metal Metal-Oxide Thin-Film Transistors Based on Indium-Tin-Zinc Oxide. <i>IEEE Electron Device Letters</i> , 2017 , 38, 894-897	4.4	15
134	Investigation of High-Performance ITO-Stabilized ZnO TFTs With Hybrid-Phase Microstructural Channels. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3174-3182	2.9	28
133	An oxidation-last annealing for enhancing the reliability of indium-gallium-zinc oxide thin-film transistors. <i>Applied Physics Letters</i> , 2017 , 110, 142102	3.4	18
132	Mechanism and Origin of Hysteresis in Oxide Thin-Film Transistor and Its Application on 3-D Nonvolatile Memory. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 438-446	2.9	41
131	Driving Stress-Induced Degradation in Polycrystalline Silicon Thin-Film Transistors and Its Suppression by a Bridged-Grain Structure. <i>IEEE Electron Device Letters</i> , 2017 , 38, 52-55	4.4	6
130	A 1200-atmosphere bulk-type all-silicon pressure sensor 2017 ,		2
129	Integrating Poly-Silicon and InGaZnO Thin-Film Transistors for CMOS Inverters. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3668-3671	2.9	30
128	Dynamic-Gate-Stress-Induced Degradation in Bridged-Grain Polycrystalline Silicon Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 3964-3970	2.9	5
127	Fabrication of High-Performance Bridged-Grain Polycrystalline Silicon TFTs by Laser Interference Lithography. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 1085-1090	2.9	11
126	Synthesis, characterization and fabrication of ultrathin iron pyrite (FeS ₂) thin films and field-effect transistors. <i>RSC Advances</i> , 2016 , 6, 8290-8296	3.7	12
125	P-22: Turn-On Voltage Modulation of Indium-Gallium-Zinc-Oxide Thin-Film Transistors through Thermal Annealing Processes. <i>Digest of Technical Papers SID International Symposium</i> , 2016 , 47, 1197-1199	2.5	3
124	High-performance staggered top-gate thin-film transistors with hybrid-phase microstructural ITO-stabilized ZnO channels. <i>Applied Physics Letters</i> , 2016 , 109, 182105	3.4	23
123	MEMS pressure sensors for high-temperature high-pressure downhole applications 2016 ,		6
122	2016 ,		22
121	Elevated-Metal Metal-Oxide Thin-Film Transistor: Technology and Characteristics. <i>IEEE Electron Device Letters</i> , 2016 , 1-1	4.4	25
120	High Precision Active-Matrix Self-Capacitive Touch Panel Based on Fluorinated ZnO Thin-Film Transistor. <i>Journal of Display Technology</i> , 2015 , 11, 22-29		9
119	. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 574-579	2.9	32
118	A Self-Scanned Active-Matrix Tactile Sensor Realized Using Silicon-Migration Technology. <i>Journal of Microelectromechanical Systems</i> , 2015 , 24, 677-684	2.5	3

117	Significant Reduction of Dynamic Negative Bias Stress-Induced Degradation in Bridged-Grain Poly-Si TFTs. <i>IEEE Electron Device Letters</i> , 2015 , 36, 141-143	4.4	7
116	Thermally Induced Variation of the Turn-ON Voltage of an IndiumGalliumZinc Oxide Thin-Film Transistor. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 3703-3708	2.9	12
115	Reversible Anion Exchange Reaction in Solid Halide Perovskites and Its Implication in Photovoltaics. <i>Journal of Physical Chemistry C</i> , 2015 , 119, 26883-26888	3.8	38
114	Identifying the Optimum Morphology in High-Performance Perovskite Solar Cells. <i>Advanced Energy Materials</i> , 2015 , 5, 1401775	21.8	57
113	Study of the Characteristics of Solid Phase Crystallized Bridged-Grain Poly-Si TFTs. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 1410-1416	2.9	10
112	Characterization of DC-Stress-Induced Degradation in Bridged-Grain Polycrystalline Silicon Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 3206-3212	2.9	12
111	A Comparative Study on the Effects of Annealing on the Characteristics of Zinc Oxide Thin-Film Transistors With Gate-Stacks of Different Gas-Permeability. <i>IEEE Electron Device Letters</i> , 2014 , 35, 841-843	4.4	19
110	The Resistivity of Zinc Oxide Under Different Annealing Configurations and Its Impact on the Leakage Characteristics of Zinc Oxide Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 1077-1084	2.9	26
109	A technology for monolithic MEMS-CMOS integration and its application to the realization of an active-matrix tactile sensor 2014 ,		2
108	Degradation of Polycrystalline Silicon TFT CMOS Inverters under AC Operation. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 295-300	2.9	2
107	Schottky Barrier Controlled Conduction in Poly-Si TFTs With Metal Source and Drain. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 1958-1964	2.9	
106	Bridged-Grain Polycrystalline Silicon Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 1965-1970	2.9	18
105	High-performance polycrystalline silicon thin-film transistors integrating sputtered aluminum-oxide gate dielectric with bridged-grain active channel. <i>Semiconductor Science and Technology</i> , 2013 , 28, 115003	1.8	8
104	High stability fluorinated zinc oxide thin film transistor and its application on high precision active-matrix touch panel 2013 ,		6
103	Self-Aligned IndiumGalliumZinc Oxide Thin-Film Transistor With Source/Drain Regions Doped by Implanted Arsenic. <i>IEEE Electron Device Letters</i> , 2013 , 34, 60-62	4.4	34
102	Characteristics of Thin-Film Transistors Fabricated on Fluorinated Zinc Oxide. <i>IEEE Electron Device Letters</i> , 2012 , 33, 549-551	4.4	32
101	Zinc-Oxide Thin-Film Transistor With Self-Aligned Source/Drain Regions Doped With Implanted Boron for Enhanced Thermal Stability. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 393-399	2.9	33
100	Analysis of Degradation Mechanisms in Low-Temperature Polycrystalline Silicon Thin-Film Transistors under Dynamic Drain Stress. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 1730-1737	2.9	24

99	Wide-band piezoresistive microphone for aero-acoustic applications 2012 ,		2
98	Bridged-Grain Solid-Phase-Crystallized Polycrystalline-Silicon Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1414-1416	4.4	32
97	Characteristics of Plasma-Fluorinated Zinc Oxide Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1147-1149	4.4	21
96	Self-Aligned Indium-Gallium-Zinc Oxide Thin-Film Transistor With Phosphorus-Doped Source/Drain Regions. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1150-1152	4.4	35
95	59.3: Bridged-grain (BG) Eximer Laser Annealing (ELA) Polycrystalline Silicon Thin Film Transistors (TFTs). <i>Digest of Technical Papers SID International Symposium</i> , 2011 , 42, 870-873	0.5	1
94	Two-Stage Degradation of p-Channel Poly-Si Thin-Film Transistors Under Dynamic Negative Bias Temperature Stress. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 3034-3041	2.9	15
93	A Two-Stage Degradation Model of p-Channel Low-Temperature Poly-Si Thin-Film Transistors Under Positive Bias Temperature Stress. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 3501-3505	2.9	6
92	Negative drain pulse stress induced two-stage degradation of P-channel poly-Si thin-film transistors 2011 ,		2
91	Positive bias temperature stress induced degradation in p-channel poly-Si thin-film transistors 2011 ,		1
90	Wide-band piezoresistive aero-acoustic microphone 2011 ,		3
89	Degradation of static behaviour of poly-Si CMOS inverters under high frequency operation 2011 ,		1
88	Series Resistance Extraction in Poly-Si TFTs With Channel Length and Mobility Variations. <i>IEEE Electron Device Letters</i> , 2011 , 32, 901-903	4.4	5
87	A New Observation of the Elliot Curve Waveform in Charge Pumping of Poly-Si TFTs. <i>IEEE Electron Device Letters</i> , 2011 , 32, 506-508	4.4	7
86	Instability of p-channel poly-Si thin-film transistors under dynamic negative bias temperature stress 2010 ,		3
85	The design, fabrication and characterization of a piezoresistive tactile sensor for fingerprint sensing 2010 ,		1
84	Metal-Induced Continuous Zonal Domain (CZD) Polycrystalline Silicon Thin-Film Transistors and Its Application on Field Sequential Color Liquid Crystal Display. <i>Journal of Display Technology</i> , 2010 , 6, 135-141		2
83	An Analytical Expression for Threshold Voltage of Polycrystalline-Silicon Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2010 , 31, 815-817	4.4	6
82	76.4: A Simple Technology for Realizing Self-Aligned Zinc Oxide Thin-Film Transistor. <i>Digest of Technical Papers SID International Symposium</i> , 2010 , 41, 1139	0.5	4

81	An Analytical Model for the Transfer Characteristics of a Polycrystalline Silicon Thin-Film Transistor With a Double Exponential Grain-Boundary Trap-State Energy Dispersion. <i>IEEE Electron Device Letters</i> , 2009 , 30, 1072-1074	4.4	7
80	A Reduced Mask-Count Technology for Complementary Polycrystalline Silicon Thin-Film Transistors With Self-Aligned Metal Electrodes. <i>IEEE Electron Device Letters</i> , 2009 , 30, 33-35	4.4	2
79	Geometric Effect Elimination and Reliable Trap State Density Extraction in Charge Pumping of Polysilicon Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2009 , 30, 517-519	4.4	11
78	. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 587-594	2.9	22
77	An Analytical Expression for the Transfer Characteristics of a Polycrystalline Silicon Thin-Film Transistor With an Undoped Channel. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 1493-1498	2.9	11
76	P-5: Self-Release Nickel Induced Lateral Crystallized (SR-NILC) Low Temperature Polycrystalline Silicon Films and Thin Film Transistors. <i>Digest of Technical Papers SID International Symposium</i> , 2009 , 40, 1096	0.5	2
75	A Quasi Two-Dimensional Conduction Model for Polycrystalline Silicon Thin-Film Transistor Based on Discrete Grains. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 2148-2156	2.9	21
74	Degradation of solution based metal induced laterally crystallized p-type poly-Si TFTS under DC bias stresses 2008 ,		2
73	Optimization of charge pumping technique in polysilicon TFTs for geometric effect elimination and trap state density extraction 2008 ,		1
72	P-230: Novel Electrical-Chemically Polished Stainless Steel Anode Organic Light Emission Device with Long Lifetime at High Luminance for Flexible Lighting. <i>Digest of Technical Papers SID International Symposium</i> , 2008 , 39, 2064	0.5	2
71	A comprehensive analytical on-current model for polycrystalline silicon thin film transistors based on effective channel mobility. <i>Journal of Applied Physics</i> , 2008 , 103, 094513	2.5	14
70	P-15: A 3 inch Active Matrix for Color Sequential- Liquid Crystal Display (CS-LCD) Based on Metal Induced Continuous Zonal Domain (CZD) Polycrystalline Silicon Technology. <i>Digest of Technical Papers SID International Symposium</i> , 2008 , 39, 1223	0.5	1
69	Passivation Effects of Aluminum on Polycrystalline Silicon Thin-Film Transistor With Metal-Replaced Junctions. <i>IEEE Electron Device Letters</i> , 2007 , 28, 126-128	4.4	
68	Degradation Behaviors of Metal-Induced Laterally Crystallized n-Type Polycrystalline Silicon Thin-Film Transistors Under DC Bias Stresses. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 225-232	2.9	34
67	An Effective Channel Mobility-Based Analytical On-Current Model for Polycrystalline Silicon Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 869-874	2.9	36
66	Polysilicon Thin Film-Transistors With Uniform and Reliable Performance Using Solution-Based Metal-Induced Crystallization. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 1244-1248	2.9	22
65	. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 3276-3284	2.9	24
64	Solution-based metal induced crystallized polycrystalline silicon films and thin-film transistors. <i>Journal of Materials Science: Materials in Electronics</i> , 2007 , 18, 117-121	2.1	3

63	Post-annealing of solution-based metal-induced laterally crystallized poly-Si with triple-frequency YAG laser. <i>Journal of Materials Science: Materials in Electronics</i> , 2007 , 18, 351-354	2.1	1
62	Effects of high temperature post-annealing on the properties of solution-based metal-induced crystallized polycrystalline silicon films. <i>Journal of Materials Science: Materials in Electronics</i> , 2007 , 18, 355-358	2.1	10
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8	Experimental investigation of electrokinetically generated in-plane vorticity in a microchannel	1
7	Parallel and series multiple microchannel systems	1
6	Investigation of heavily doped silicon as an anode material for top-emitting organic light-emitting diode	1
5	Suppression of leakage current in low-temperature metal-induced unilaterally crystallized polycrystalline silicon thin-film transistor using an improved process sequence and a gate-modulated lightly-doped drain structure	1
4	Application of metal-induced unilaterally crystallized polycrystalline silicon thin-film transistor technology to active-matrix organic light-emitting diode displays	1
3	Reduction of threshold voltage in metal-induced-laterally-crystallized thin film transistors	3
2	Implementation of linear doping profiles for high voltage thin-film SOI devices	8
1	Effect of Moisture Exchange Caused by Low-Temperature Annealing on Device Characteristics and Instability in InSnZnO Thin-Film Transistors. <i>Advanced Materials Interfaces</i> ,2102584	4.6